

# MMBT5401LT1G, SMMBT5401LT1G, MMBT5401LT3G



ON Semiconductor®

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## High Voltage Transistor

PNP Silicon

### Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS

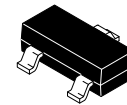
Rating	Symbol	Value	Unit
Collector - Emitter Voltage	$V_{CEO}$	-150	Vdc
Collector - Base Voltage	$V_{CBO}$	-160	Vdc
Emitter - Base Voltage	$V_{EBO}$	-5.0	Vdc
Collector Current - Continuous	$I_C$	-500	mAdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

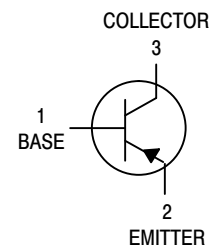
### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate Above $25^\circ\text{C}$	$P_D$	225	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate Above $25^\circ\text{C}$	$P_D$	300	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

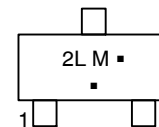
1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
2. Alumina =  $0.4 \times 0.3 \times 0.024$  in 99.5% alumina.



SOT-23 (TO-236)  
CASE 318  
STYLE 6



### MARKING DIAGRAM



2L = Specific Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

### ORDERING INFORMATION

Device	Package	Shipping†
MMBT5401LT1G	SOT-23 (Pb-Free)	3,000 Tape & Reel
SMMBT5401LT1G	SOT-23 (Pb-Free)	3,000 Tape & Reel
MMBT5401LT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MMBT5401LT1G, SMMBT5401LT1G, MMBT5401LT3G

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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### OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (I <sub>C</sub> = -1.0 mA <sub>dc</sub> , I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	-150	–	V <sub>dc</sub>
Collector–Base Breakdown Voltage (I <sub>C</sub> = -100 μA <sub>dc</sub> , I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	-160	–	V <sub>dc</sub>
Emitter–Base Breakdown Voltage (I <sub>E</sub> = -10 μA <sub>dc</sub> , I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	-5.0	–	V <sub>dc</sub>
Collector–Base Cutoff Current (V <sub>CB</sub> = -120 V <sub>dc</sub> , I <sub>E</sub> = 0) (V <sub>CB</sub> = -120 V <sub>dc</sub> , I <sub>E</sub> = 0, T <sub>A</sub> = 100°C)	I <sub>CBO</sub>	–	-50	nA <sub>dc</sub> μA <sub>dc</sub>

### ON CHARACTERISTICS

DC Current Gain (I <sub>C</sub> = -1.0 mA <sub>dc</sub> , V <sub>CE</sub> = -5.0 V <sub>dc</sub> ) (I <sub>C</sub> = -10 mA <sub>dc</sub> , V <sub>CE</sub> = -5.0 V <sub>dc</sub> ) (I <sub>C</sub> = -50 mA <sub>dc</sub> , V <sub>CE</sub> = -5.0 V <sub>dc</sub> )	h <sub>FE</sub>	50 60 50	– 240 –	–
Collector–Emitter Saturation Voltage (I <sub>C</sub> = -10 mA <sub>dc</sub> , I <sub>B</sub> = -1.0 mA <sub>dc</sub> ) (I <sub>C</sub> = -50 mA <sub>dc</sub> , I <sub>B</sub> = -5.0 mA <sub>dc</sub> )	V <sub>CE(sat)</sub>	– –	-0.2 -0.5	V <sub>dc</sub>
Base–Emitter Saturation Voltage (I <sub>C</sub> = -10 mA <sub>dc</sub> , I <sub>B</sub> = -1.0 mA <sub>dc</sub> ) (I <sub>C</sub> = -50 mA <sub>dc</sub> , I <sub>B</sub> = -5.0 mA <sub>dc</sub> )	V <sub>BE(sat)</sub>	– –	-1.0 -1.0	V <sub>dc</sub>

### SMALL-SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product (I <sub>C</sub> = -10 mA <sub>dc</sub> , V <sub>CE</sub> = -10 V <sub>dc</sub> , f = 100 MHz)	f <sub>T</sub>	100	300	MHz
Output Capacitance (V <sub>CB</sub> = -10 V <sub>dc</sub> , I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	–	6.0	pF
Small Signal Current Gain (I <sub>C</sub> = -1.0 mA <sub>dc</sub> , V <sub>CE</sub> = -10 V <sub>dc</sub> , f = 1.0 kHz)	h <sub>fe</sub>	40	200	–
Noise Figure (I <sub>C</sub> = -200 μA <sub>dc</sub> , V <sub>CE</sub> = -5.0 V <sub>dc</sub> , R <sub>S</sub> = 10 Ω, f = 1.0 kHz)	NF	–	8.0	dB

# MMBT5401LT1G, SMMBT5401LT1G, MMBT5401LT3G

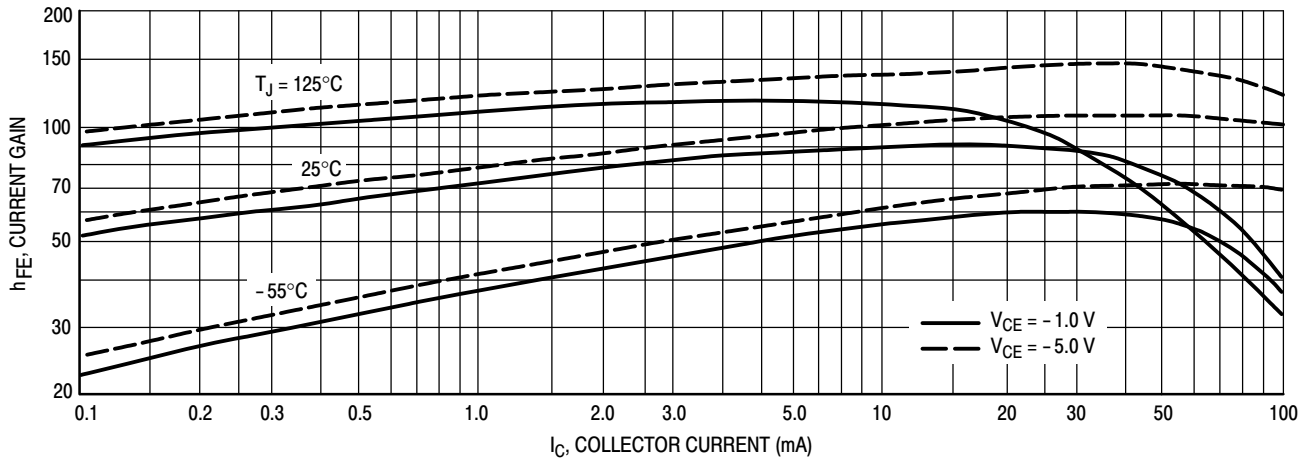


Figure 1. DC Current Gain

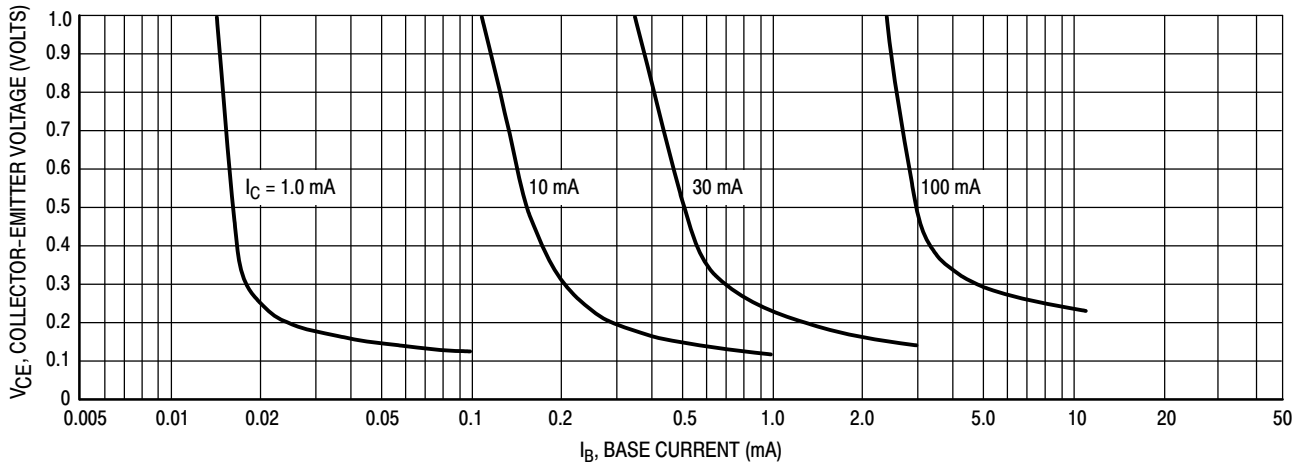


Figure 2. Collector Saturation Region

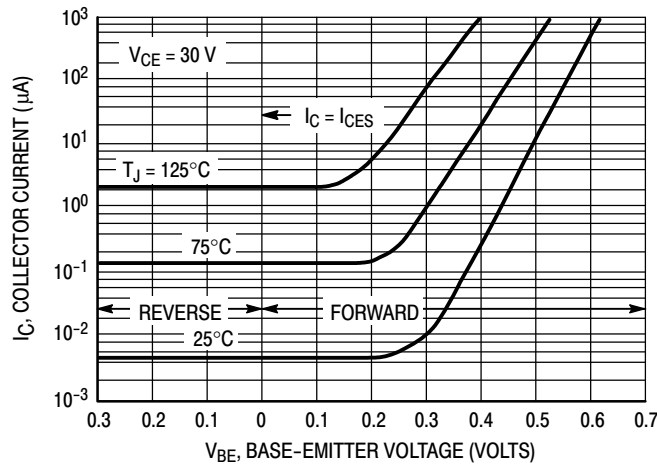


Figure 3. Collector Cut-Off Region

MMBT5401LT1G, SMMBT5401LT1G, MMBT5401LT3G

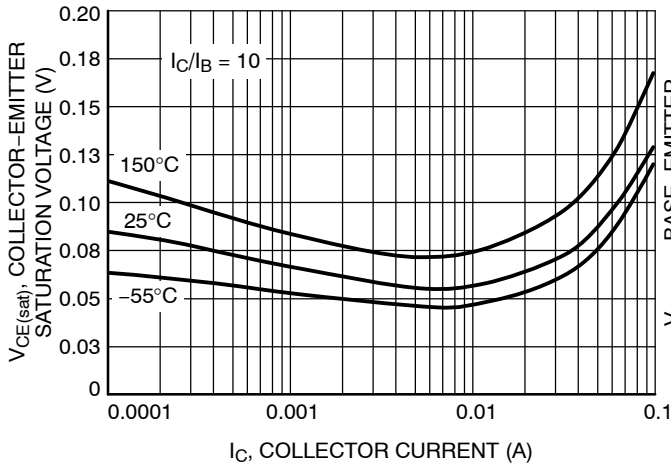


Figure 4. Collector Emitter Saturation Voltage vs. Collector Current

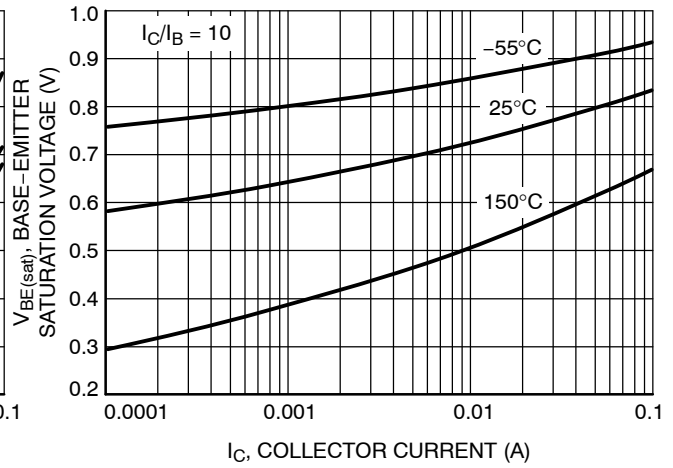


Figure 5. Base Emitter Saturation Voltage vs. Collector Current

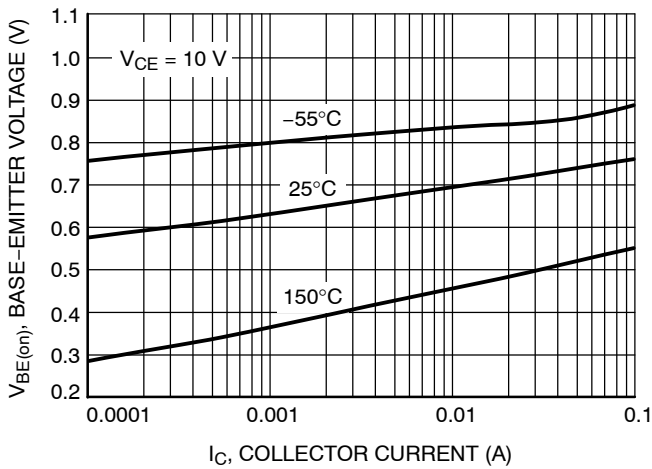


Figure 6. Base Emitter Voltage vs. Collector Current

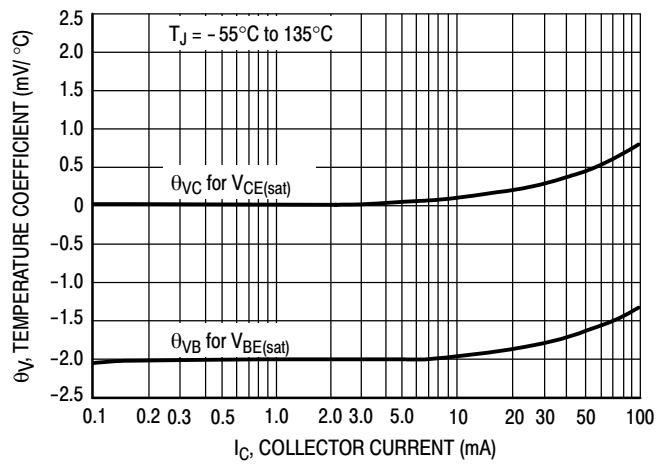


Figure 7. Temperature Coefficients

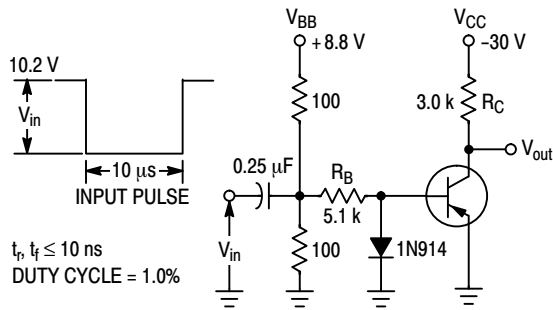


Figure 8. Switching Time Test Circuit

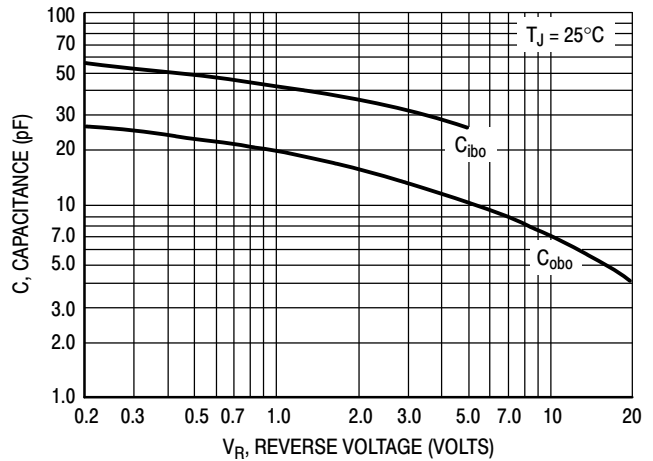


Figure 9. Capacitances

MMBT5401LT1G, SMMBT5401LT1G, MMBT5401LT3G

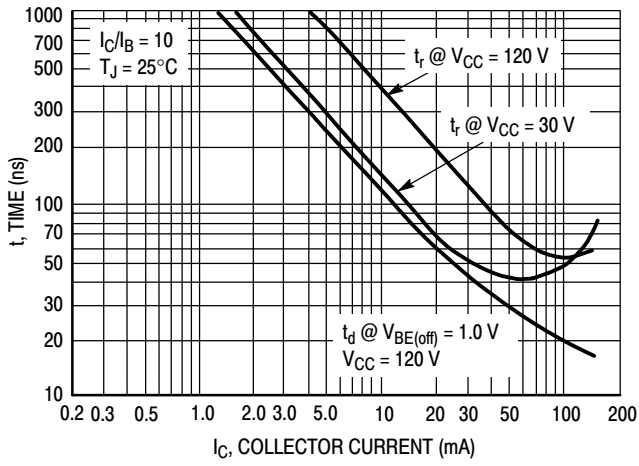


Figure 10. Turn-On Time

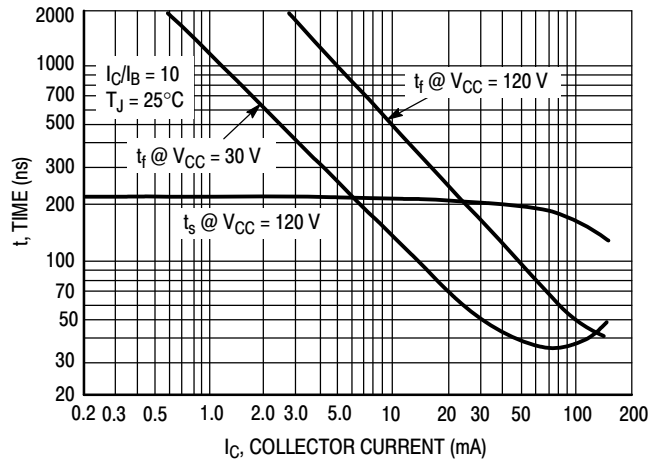


Figure 11. Turn-Off Time

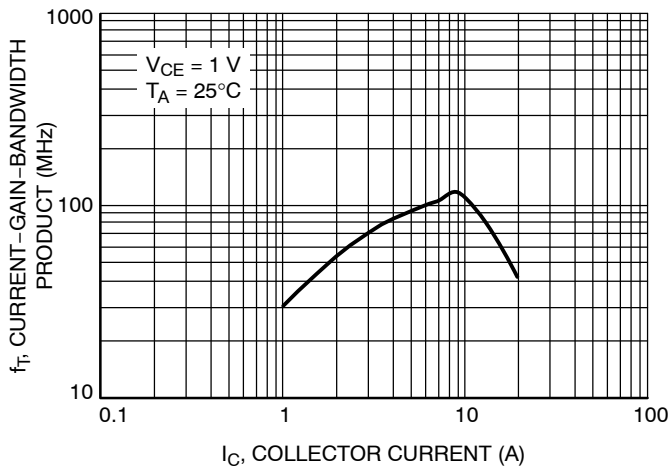


Figure 12. Current Gain Bandwidth Product

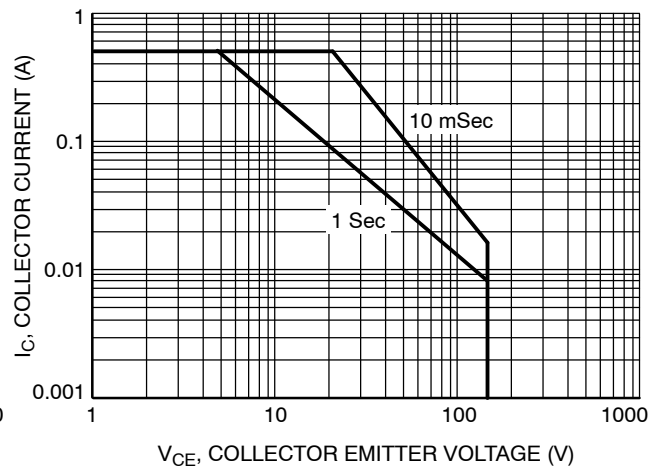
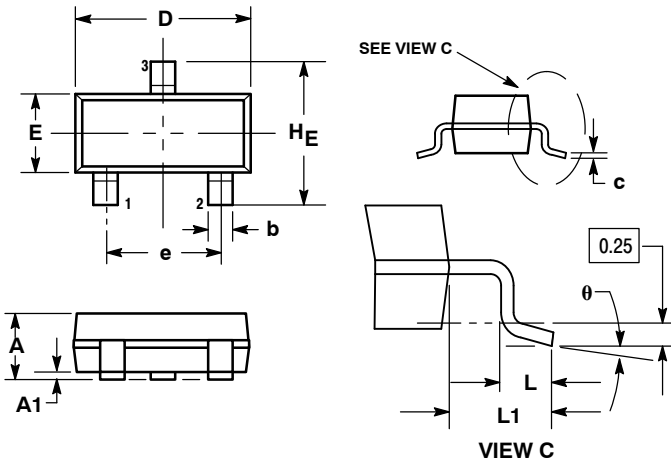


Figure 13. Safe Operating Area

# MMBT5401LT1G, SMMBT5401LT1G, MMBT5401LT3G

## PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AP



NOTES:

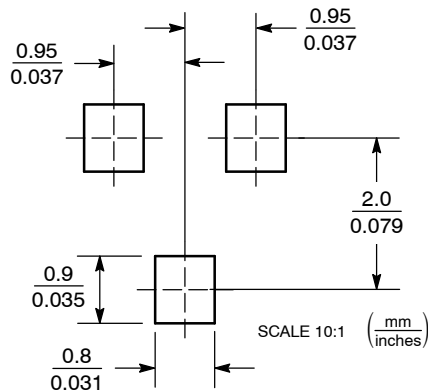
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

STYLE 6:

- PIN 1. BASE
- EMITTER
- COLLECTOR

### SOLDERING FOOTPRINT



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